

# H5N1506P

Silicon N Channel MOS FET  
High Speed Power Switching

REJ03G0389-0200

Rev.2.00

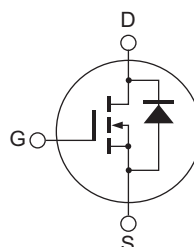
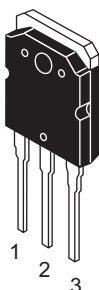
Jul 03, 2006

## Features

- Low on-resistance
- Low leakage current
- High speed switching

## Outline

RENESAS Package code: PRSS0004ZE-A  
(Package name: TO-3P)



1. Gate
2. Drain (Flange)
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source voltage	$V_{DSS}$	150	V
Gate to Source voltage	$V_{GSS}$	±30	V
Drain current	$I_D$	98	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	294	A
Body-Drain diode reverse Drain current	$I_{DR}$	98	A
Body-Drain diode reverse Drain peak current	$I_{DR(pulse)}$ <sup>Note1</sup>	294	A
Avalanche current	$I_{AP}$ <sup>Note3</sup>	48	A
Avalanche energy	$E_{AR}$ <sup>Note3</sup>	172	mJ
Channel dissipation	$P_{ch}$ <sup>Note2</sup>	150	W
Channel to case thermal impedance	$\theta_{ch-c}$	0.833	°C/W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$

2. Value at  $T_c = 25^\circ C$

3.  $STch = 25^\circ C$ ,  $T_{ch} \leq 150^\circ C$

## Electrical Characteristics

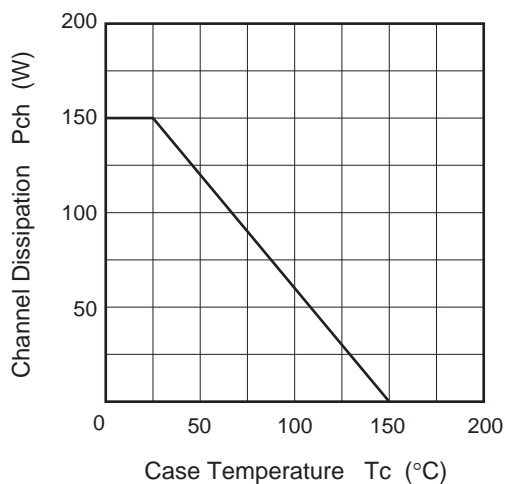
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	150	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Zero Gate voltage Drain current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 150 \text{ V}$ , $V_{GS} = 0$
Gate to Source leak current	$I_{GSS}$	—	—	$\pm 0.1$	$\mu\text{A}$	$V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$
Forward transfer admittance	$ y_{fs} $	36	60	—	S	$I_D = 47.5 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note4</sup>
Static Drain to Source on state resistance	$R_{DS(on)}$	—	0.014	0.016	$\Omega$	$I_D = 47.5 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	4900	—	pF	$V_{DS} = 25 \text{ V}$ $V_{GS} = 0$ $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	1000	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	120	—	pF	
Turn-on delay time	$t_{d(on)}$	—	60	—	ns	$I_D = 47.5 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 1.58 \Omega$ $R_g = 10 \Omega$
Rise time	$t_r$	—	380	—	ns	
Turn-off delay time	$t_{d(off)}$	—	220	—	ns	
Fall time	$t_f$	—	250	—	ns	
Total Gate charge	$Q_g$	—	100	—	nC	$V_{DD} = 120 \text{ V}$ $V_{GS} = 10 \text{ V}$ $I_D = 95 \text{ A}$
Gate to Source charge	$Q_{gs}$	—	24	—	nC	
Gate to Drain charge	$Q_{gd}$	—	45	—	nC	
Body-Drain diode forward voltage	$V_{DF}$	—	1.0	1.5	V	$I_F = 95 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>
Body-Drain diode reverse recovery time	$t_{rr}$	—	150	—	ns	$I_F = 95 \text{ A}$ , $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$
Body-Drain diode reverse recovery charge	$Q_{rr}$	—	1.0	—	$\mu\text{C}$	

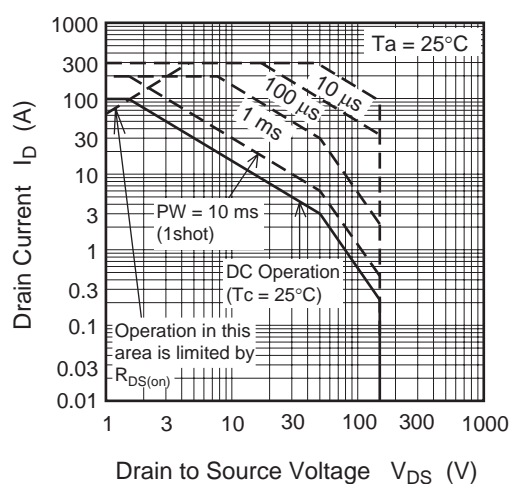
Notes: 4. Pulse test

## Main Characteristics

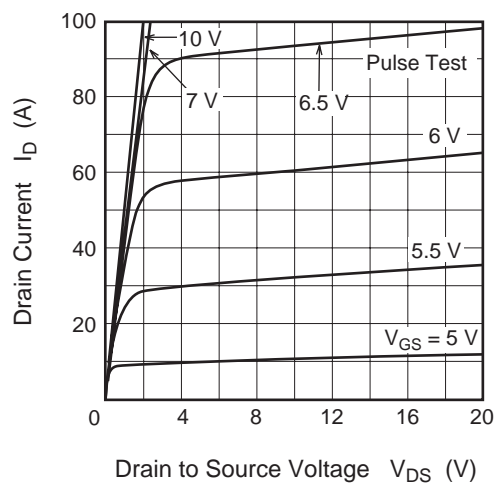
Power vs. Temperature Derating



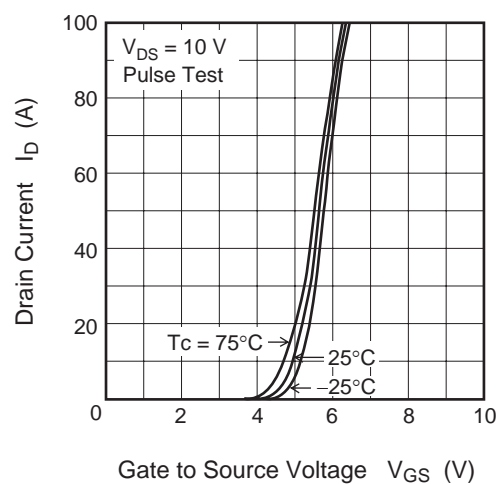
Maximum Safe Operation Area



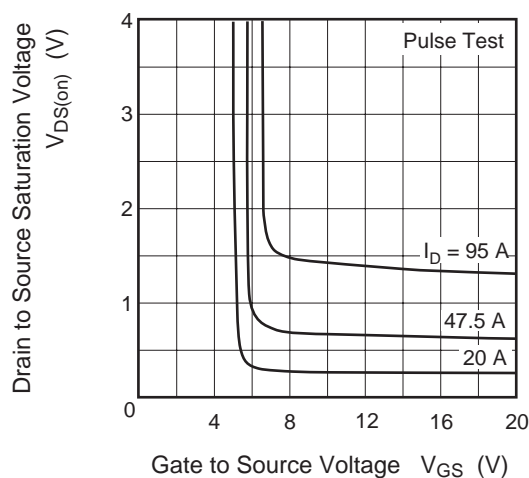
Typical Output Characteristics



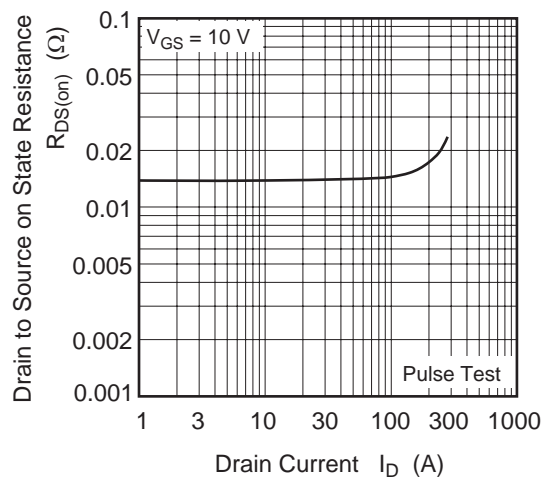
Typical Transfer Characteristics

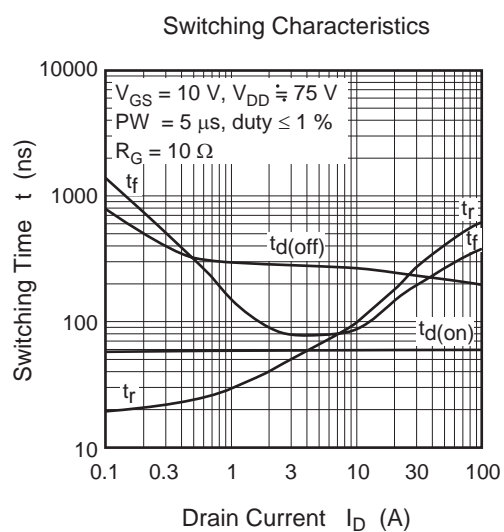
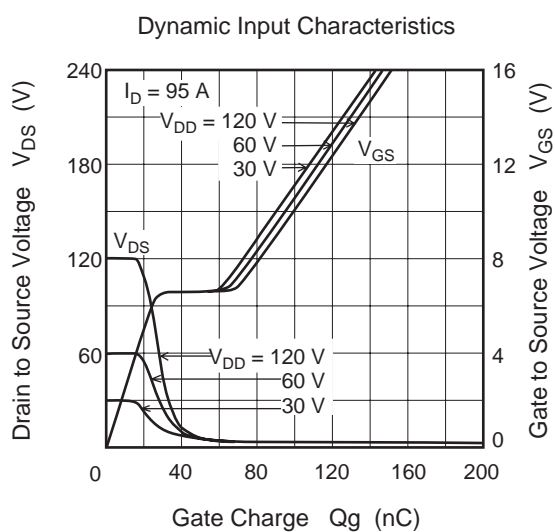
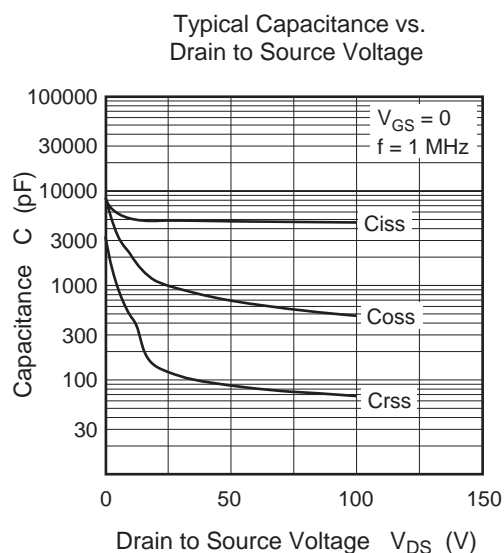
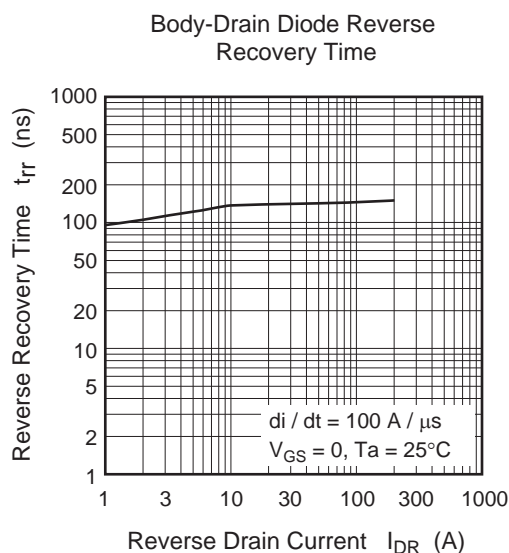
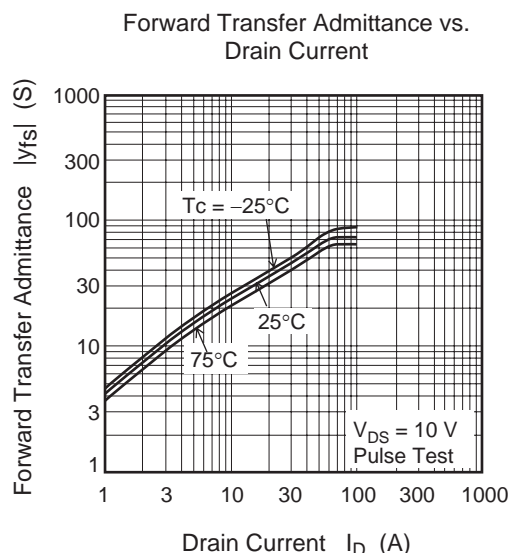
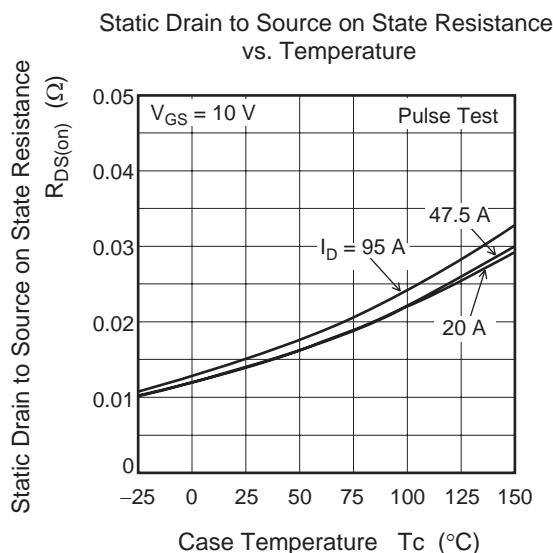


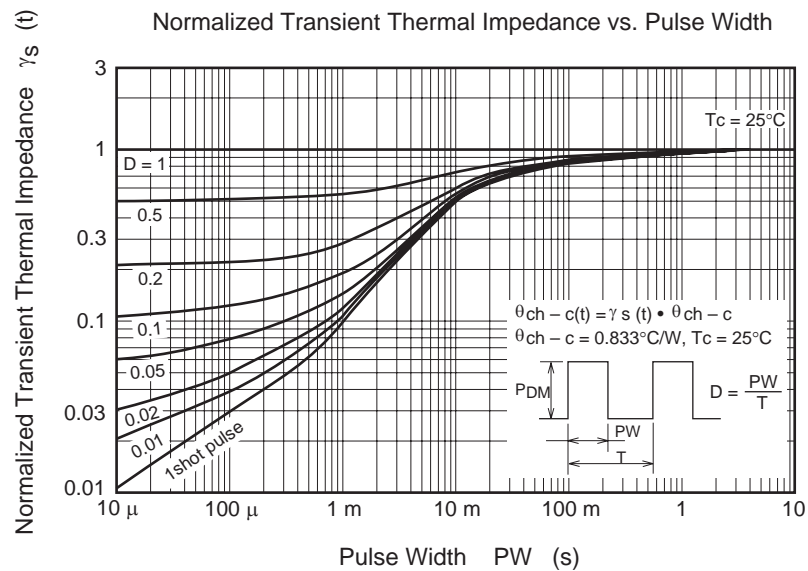
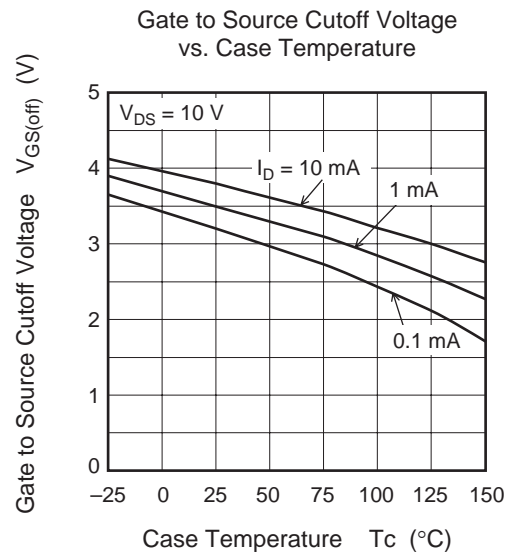
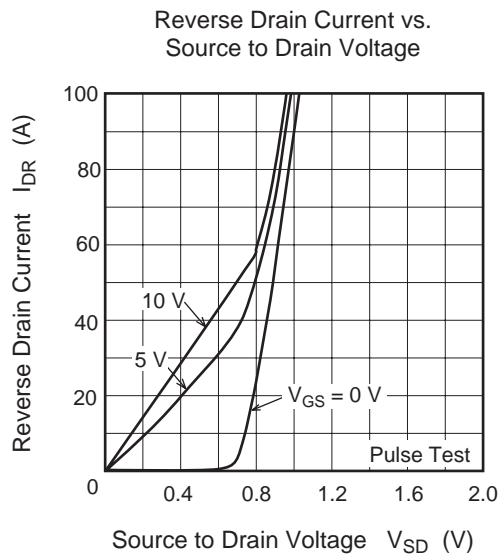
Drain to Source Saturation Voltage vs. Gate to Source Voltage



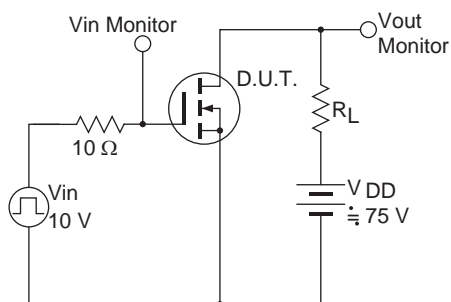
Static Drain to Source on State Resistance vs. Drain Current



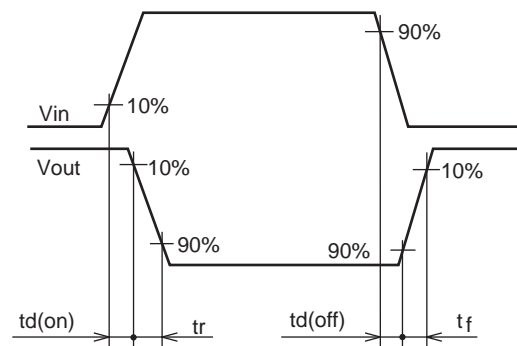




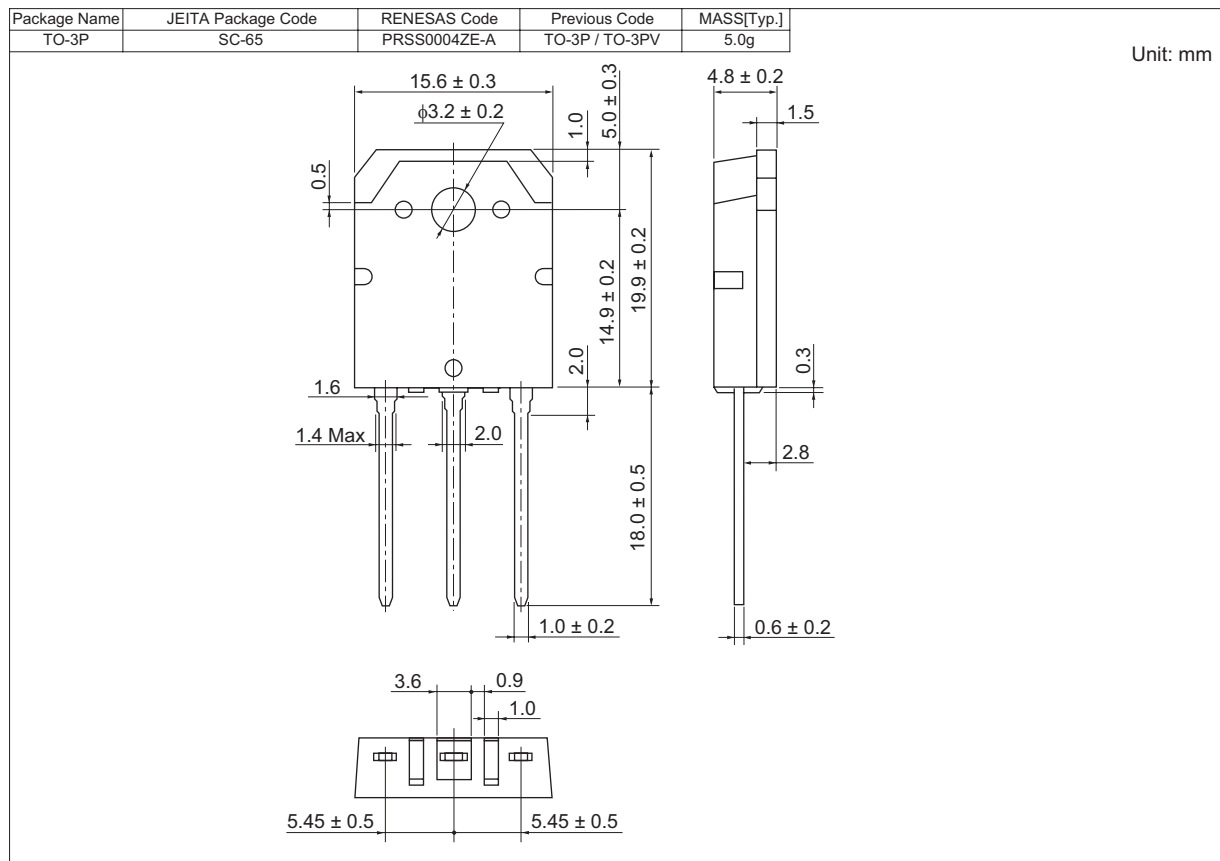
Switching Time Test Circuit



Waveform



## Package Dimensions



## Ordering Information

Part Name	Quantity	Shipping Container
H5N1506P-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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